

# NTHD3133PF

## Power MOSFET and Schottky Diode

-20 V, FETKY™, P-Channel, -4.4 A, with 3.7 A Schottky Barrier Diode, ChipFET™



ON Semiconductor®

<http://onsemi.com>

### Features

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP-6 Package
- Leadless SMD Package Provides Great Thermal Characteristics
- Independent Pinout to each Device to Ease Circuit Design
- Trench P-Channel for Low On Resistance
- Ultra Low  $V_F$  Schottky
- These are Pb-Free Devices

### Applications

- Li-Ion Battery Charging
- High Side DC-DC Conversion Circuits
- High Side Drive for Small Brushless DC Motors
- Power Management in Portable, Battery Powered Products

### MOSFET MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-to-Source Voltage	$V_{DSS}$	-20	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 8.0$	V
Continuous Drain Current (Note 1)	Steady State	$T_J = 25^\circ\text{C}$	$I_D$ -3.2
		$T_J = 85^\circ\text{C}$	-2.3
		$t \leq 5$ s	$T_J = 25^\circ\text{C}$
Power Dissipation (Note 1)	Steady State	$T_J = 25^\circ\text{C}$	$P_D$ 1.1
			$t \leq 5$ s
Pulsed Drain Current	$t_p = 10$ $\mu\text{s}$	$I_{DM}$ -13	A
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	2.5	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

### SCHOTTKY DIODE MAXIMUM RATINGS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	20	V
DC Blocking Voltage	$V_R$	20	V
Average Rectified Forward Current	Steady State	$T_J = 25^\circ\text{C}$	$I_F$ 2.2
			$t \leq 5$ s

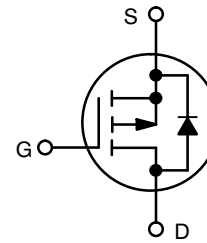
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

MOSFET		
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ MAX
-20 V	64 m $\Omega$ @ -4.5 V	-4.4 A
	85 m $\Omega$ @ -2.5 V	

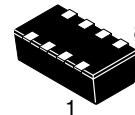
SCHOTTKY DIODE		
$V_R$ MAX	$V_F$ TYP	$I_F$ MAX
20 V	0.35 V	3.7 A



P-Channel MOSFET

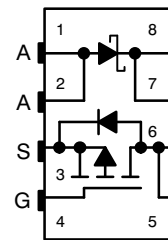


Schottky Diode

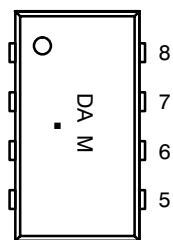


ChipFET  
CASE 1206A  
STYLE 3

### PIN CONNECTIONS



### MARKING DIAGRAM



- DA = Specific Device Code
- M = Month Code
- = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# NTHD3133PF

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	113	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 10$ s (Note 2)	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$

2. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
-----------	--------	-----------------	-----	-----	-----	-------

### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-15		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1.0	$\mu\text{A}$
					-5.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.45		-1.5	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.7		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -3.2\text{ A}$		64	80	$\text{m}\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -2.2\text{ A}$		85	110	
		$V_{GS} = -1.8\text{ V}, I_D = -1.0\text{ A}$		120	170	
Forward Transconductance	$g_{FS}$	$V_{DS} = -10\text{ V}, I_D = -2.9\text{ A}$		8.0		S

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -10\text{ V}$		680		$\text{pF}$
Output Capacitance	$C_{OSS}$			100		
Reverse Transfer Capacitance	$C_{RSS}$			70		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -3.2\text{ A}$		7.4		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	$Q_{GS}$			1.4		
Gate-to-Drain Charge	$Q_{GD}$			2.5		

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -3.2\text{ A}, R_G = 2.4\ \Omega$		5.8		ns
Rise Time	$t_r$			11.7		
Turn-Off Delay Time	$t_{d(OFF)}$			16		
Fall Time	$t_f$			12.4		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -2.5\text{ A}$	$T_J = 25^{\circ}\text{C}$		-0.8	-1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}, di_S/dt = 100\text{ A}/\mu\text{s}$			13.5		ns
Charge Time	$t_a$				9.5		
Discharge Time	$t_b$				4.0		
Reverse Recovery Charge	$Q_{RR}$				6.5		

### SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Maximum Instantaneous Forward Voltage	$V_F$	$I_F = 0.1\text{ A}$			0.31	V
		$I_F = 1.0\text{ A}$			0.365	
Maximum Instantaneous Reverse Current	$I_R$	$V_R = 10\text{ V}$			0.75	mA
		$V_R = 20\text{ V}$			2.5	
Non-Repetitive Peak Surge Current	$I_{FSM}$	Halfwave, Single Pulse 60 Hz			23	A

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

# NTHD3133PF

## TYPICAL P-CHANNEL PERFORMANCE CURVES

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

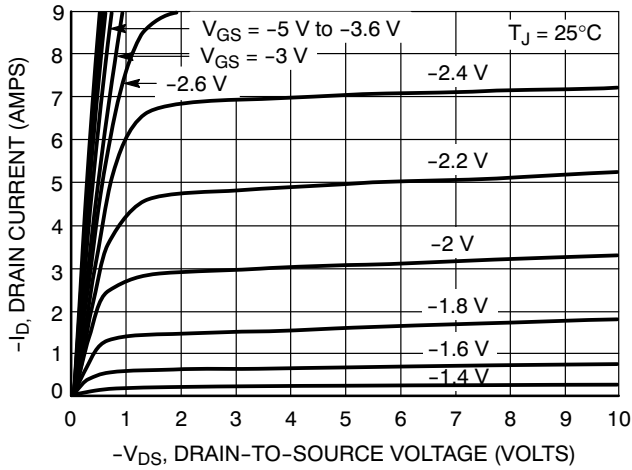


Figure 1. On-Region Characteristics

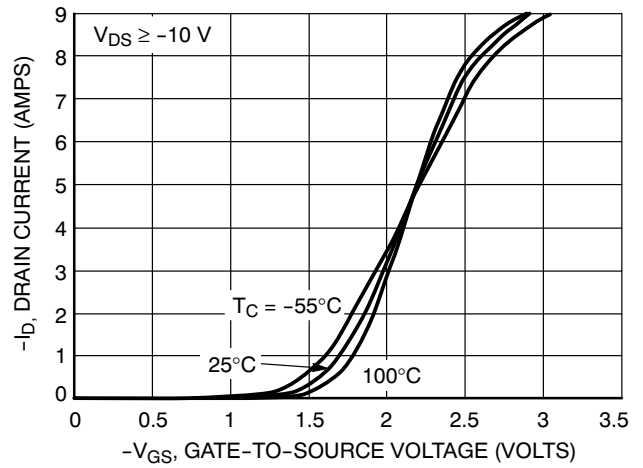


Figure 2. Transfer Characteristics

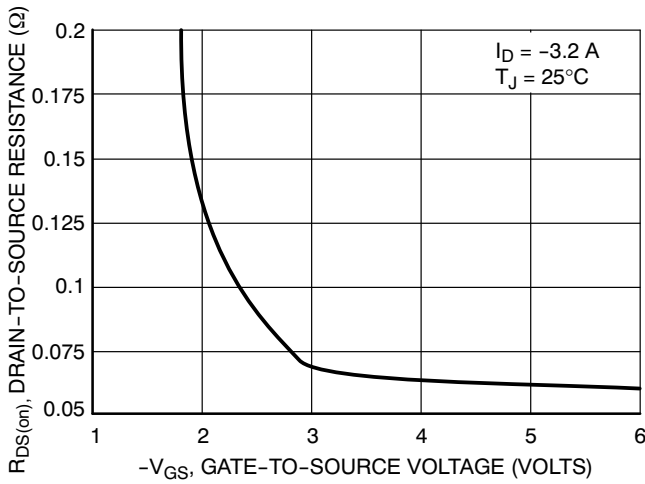


Figure 3. On-Resistance vs. Gate-to-Source Voltage

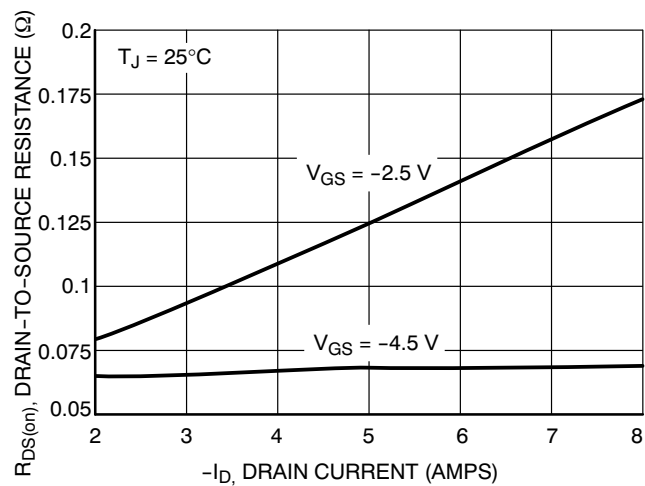


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

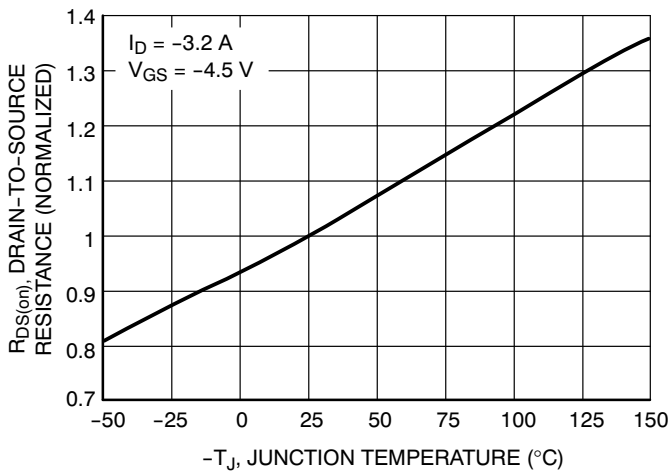


Figure 5. On-Resistance Variation with Temperature

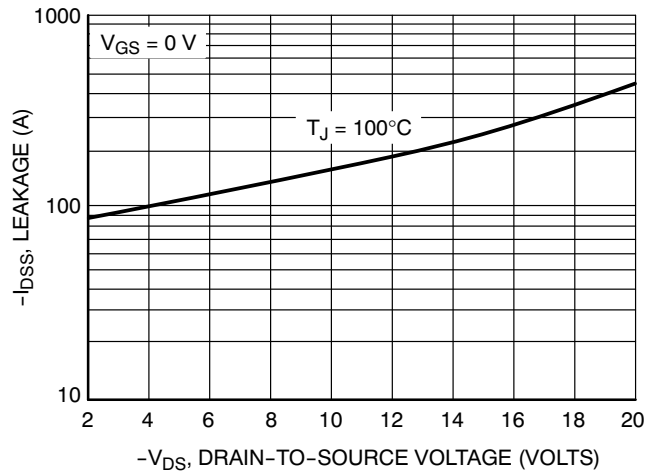


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTHD3133PF

## TYPICAL P-CHANNEL PERFORMANCE CURVES

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

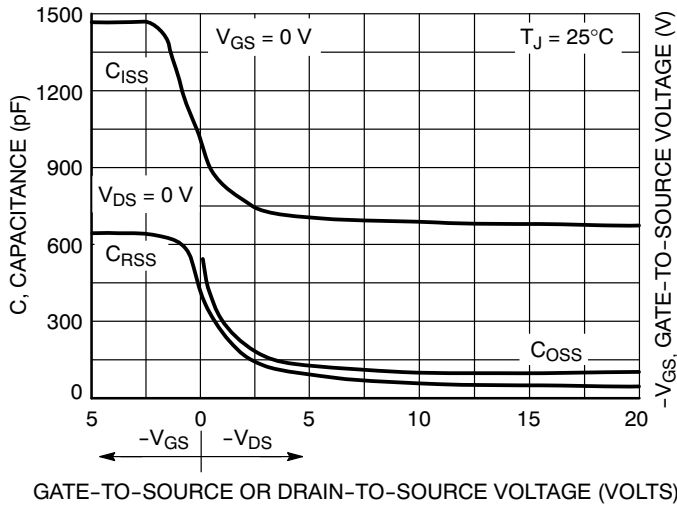


Figure 7. Capacitance Variation

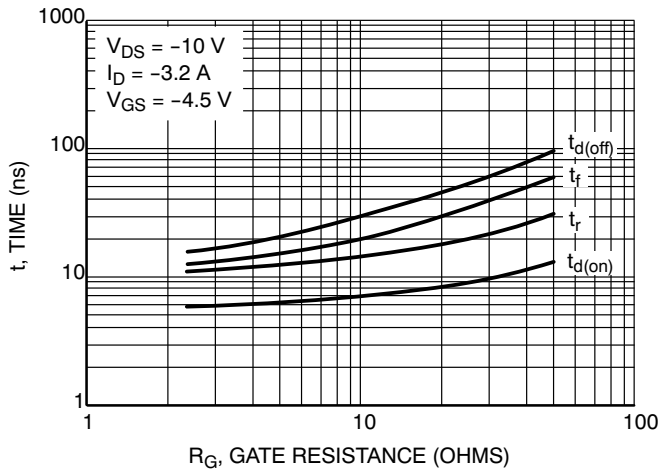


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

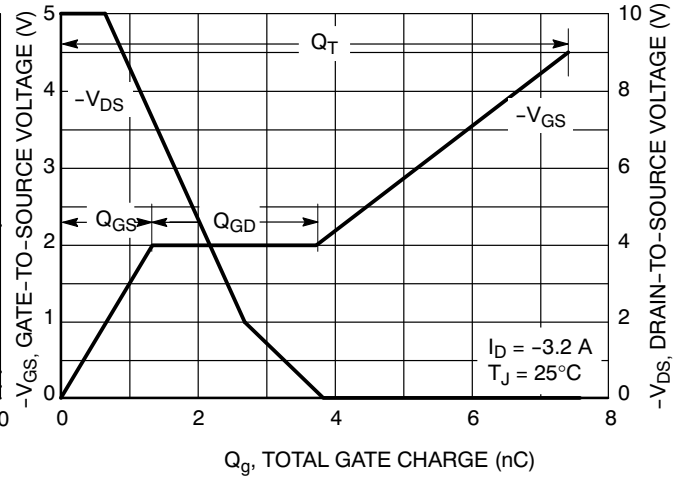


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

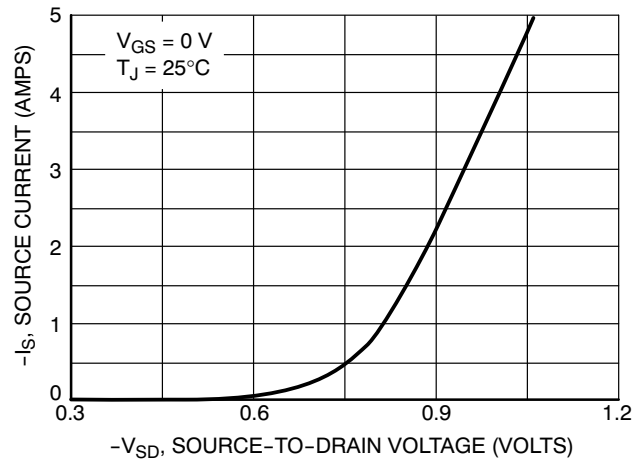


Figure 10. Diode Forward Voltage vs. Current

# NTHD3133PF

## TYPICAL SCHOTTKY PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

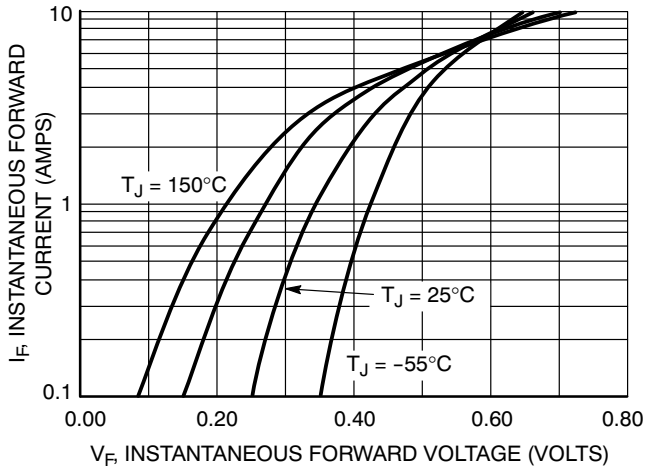


Figure 11. Typical Forward Voltage

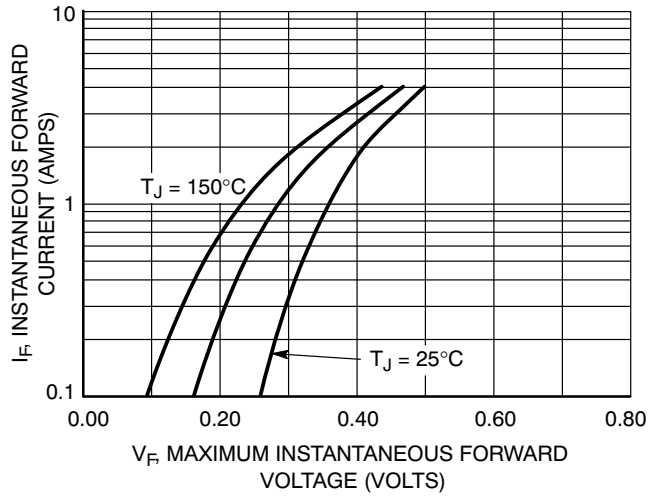


Figure 12. Maximum Forward Voltage

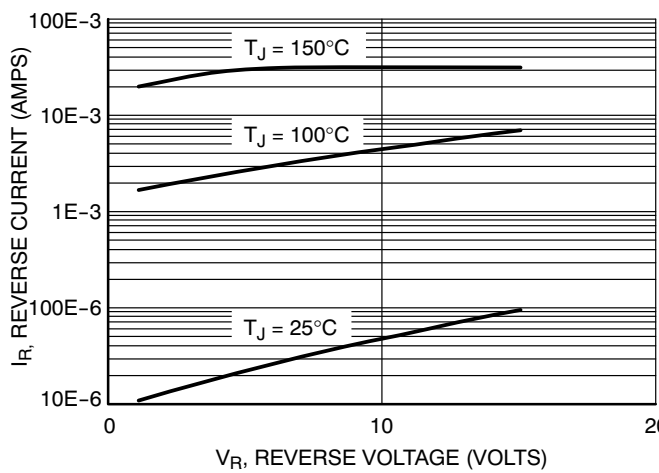


Figure 13. Typical Reverse Current

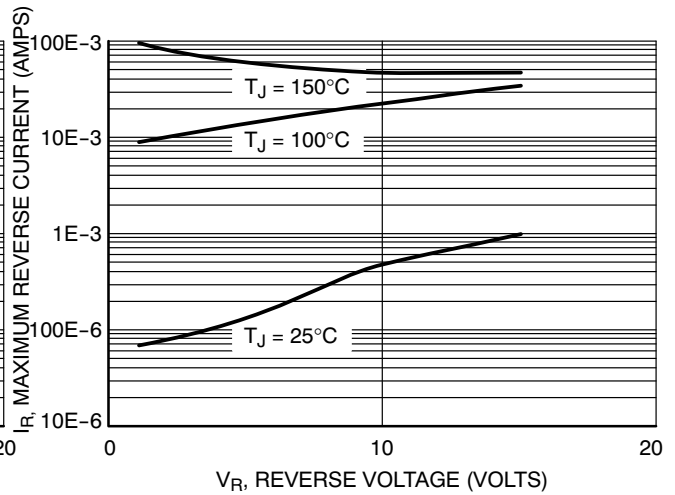


Figure 14. Maximum Reverse Current

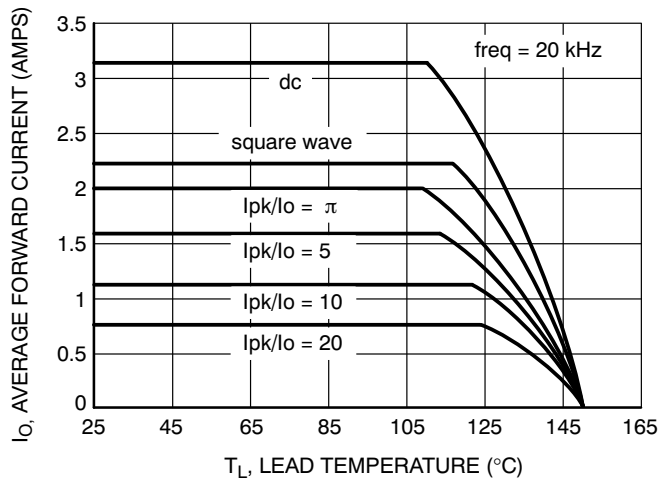


Figure 15. Current Derating

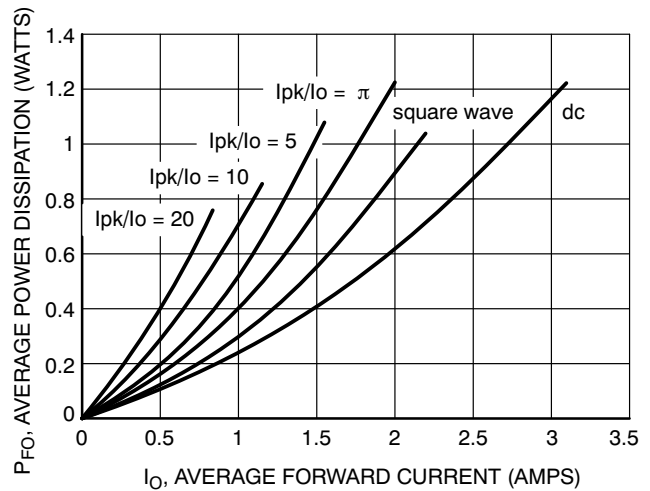


Figure 16. Forward Power Dissipation

# NTHD3133PF

## DEVICE ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTHD3133PFT1G	ChipFET (Pb-Free)	3000 / Tape & Reel
NTHD3133PFT3G	ChipFET (Pb-Free)	10000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ChipFET is a trademark of Vishay Siliconix.  
FETKY is a registered trademark of International Rectifier Corporation.

# MECHANICAL CASE OUTLINE

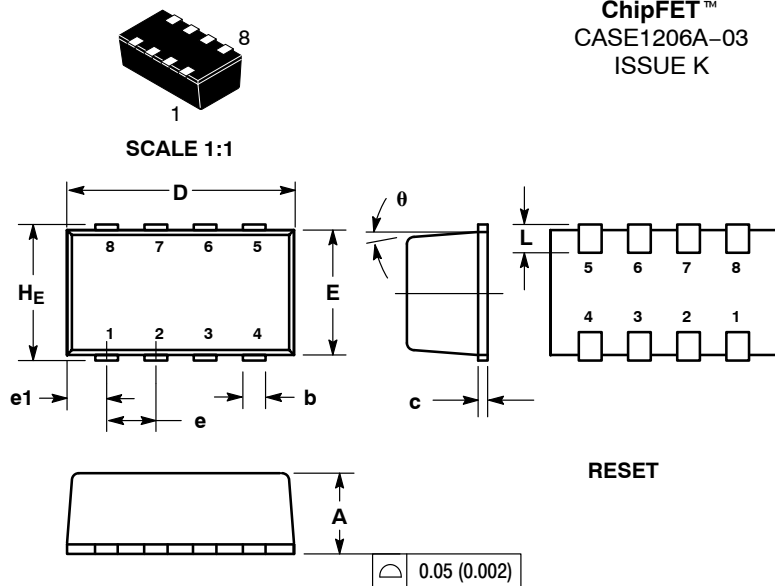
## PACKAGE DIMENSIONS

ON Semiconductor®



ChipFET™  
CASE1206A-03  
ISSUE K

DATE 19 MAY 2009

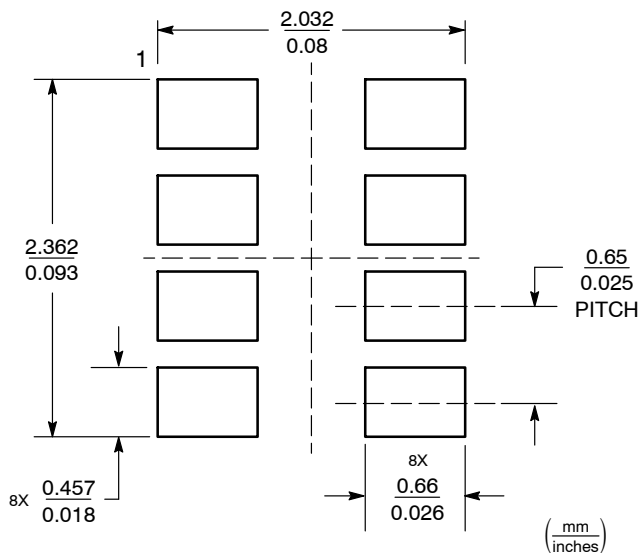


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
  4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
  5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
  6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
HE	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

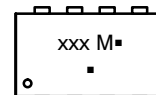
- |   |   |   |  |   |   |
|---|---|---|--|---|---|
| <p>STYLE 1:<br/>PIN 1. DRAIN<br/>2. DRAIN<br/>3. DRAIN<br/>4. GATE<br/>5. SOURCE<br/>6. DRAIN<br/>7. DRAIN<br/>8. DRAIN</p> | <p>STYLE 2:<br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. SOURCE 2<br/>4. GATE 2<br/>5. DRAIN 2<br/>6. DRAIN 2<br/>7. DRAIN 1<br/>8. DRAIN 1</p> | <p>STYLE 3:<br/>PIN 1. ANODE<br/>2. ANODE<br/>3. SOURCE<br/>4. GATE<br/>5. DRAIN<br/>6. DRAIN<br/>7. CATHODE<br/>8. CATHODE</p> | <p>STYLE 4:<br/>PIN 1. COLLECTOR<br/>2. COLLECTOR<br/>3. COLLECTOR<br/>4. BASE<br/>5. EMITTER<br/>6. COLLECTOR<br/>7. COLLECTOR<br/>8. COLLECTOR</p> | <p>STYLE 5:<br/>PIN 1. ANODE<br/>2. ANODE<br/>3. DRAIN<br/>4. DRAIN<br/>5. SOURCE<br/>6. GATE<br/>7. CATHODE<br/>8. CATHODE</p> | <p>STYLE 6:<br/>PIN 1. ANODE<br/>2. DRAIN<br/>3. DRAIN<br/>4. GATE<br/>5. SOURCE<br/>6. DRAIN<br/>7. DRAIN<br/>8. CATHODE / DRAIN</p> |
|---|---|---|--|---|---|

### SOLDERING FOOTPRINT



Basic Style

### GENERIC MARKING DIAGRAM\*



- xxx = Specific Device Code
  - M = Month Code
  - = Pb-Free Package
- (Note: Microdot may be in either location)

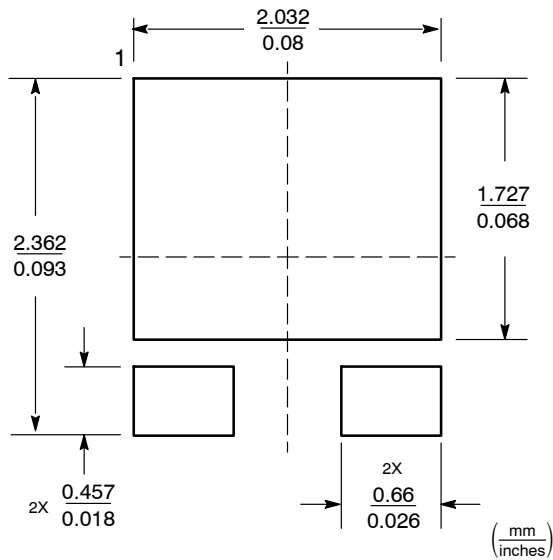
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### OPTIONAL SOLDERING FOOTPRINTS ON PAGE 2

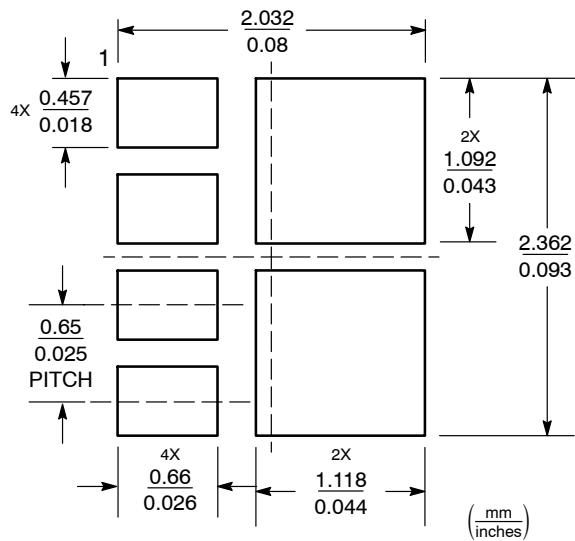
DOCUMENT NUMBER:	98AON03078D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	ChipFET	PAGE 1 OF 2

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

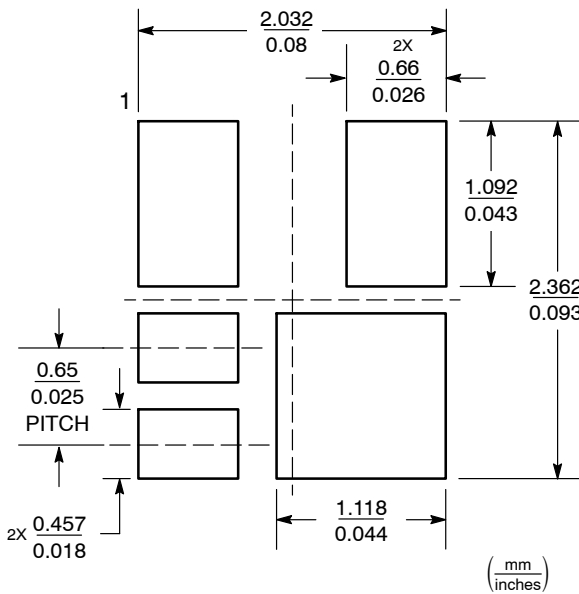
ADDITIONAL SOLDERING FOOTPRINTS\*



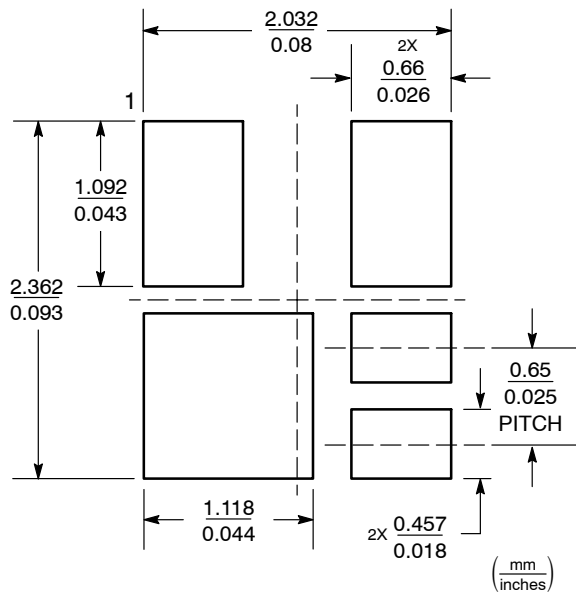
Styles 1 and 4



Style 2



Style 3



Style 5

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON03078D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	ChipFET	PAGE 2 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**onsemi Website:** [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

**North American Technical Support:**  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

**Europe, Middle East and Africa Technical Support:**

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative